

Supplementary Information

The convenient synthesis and applications of gram scale boron nitride nanosheets

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Fig. SI 1. The digital images of the as-prepared S₁ (a) and S₂ (b). S₂ (0.66g~1g) was prepared by using 40 mmol B₂O₃, 200 mmol zinc powder and 50 mmol N₂H₄·2HCl

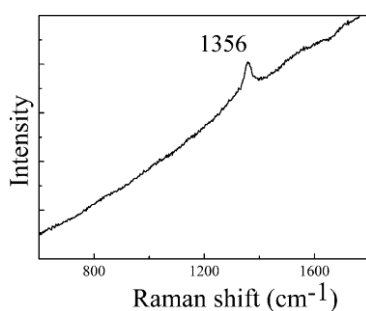


Fig. SI 2. Raman spectrum of the as-prepared S₁.

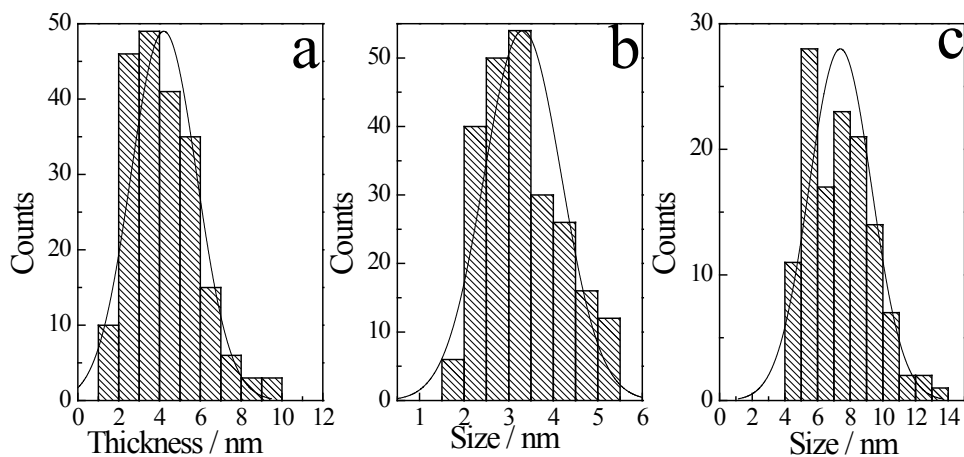


Fig. SI 3. (a) Thickness distribution of S₁, Au particles sizes distribution on the BNNSs with (b) and without (c) H₂O₂ treatment.

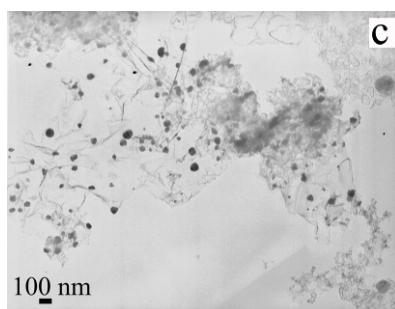


Fig. SI 4. Typical TEM image of 16% Pt/BNNSs

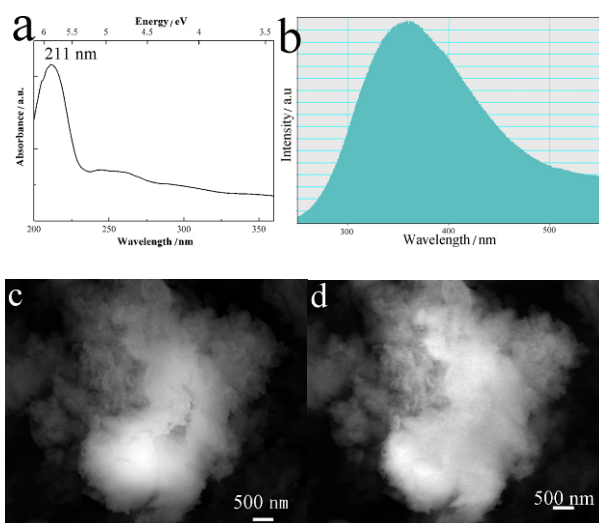


Fig. SI 5. The optical absorption spectrum (a) and CL spectrum (b) of S₁ measured at room temperature. The optical absorption spectrum shows a peak centered at 211 nm (5.9 eV). The strong CL luminescence emission in the ultraviolet range (around 370 nm, 3.35 eV) can be attributed to the deep-level emissions associated with structure defects. SEM image of S₁ (c) and corresponding CL luminescence image (d), indicating the uniform optical properties across the sample.